

FINAL PRODUCT/PROCESS CHANGE NOTIFICATION Generic Copy

18-APR-2005

SUBJECT: ON Semiconductor Final Product/Process Change Notification #14065

TITLE: Final Notification for IPCN#12477 - High Frequency Transfer to ISMF

EFFECTIVE DATE: 18-Jun-2005

AFFECTED CHANGE CATEGORY: ON Semiconductor Fab Site

AFFECTED PRODUCT DIVISION: Discretes Products

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Laura Rivers <\$20636@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office or Donald Barlow <R39117@onsemi.com>

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact Sales Office or Donald Barlow <R39117@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 60 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact your local ON Semiconductor Sales Office.

DESCRIPTION AND PURPOSE:

This is the Final Notification for a portion of the devices listed in IPCN #12477 - High Frequency, High Voltage NPN Transistors and Switching Diode Transfer from Panjit Fab to ISMF Fab.

This Notification only applies to the devices listed below.

The list represents a small portion of the High Frequency transistors family. There will be subsequent final notifications for the remainder of the devices listed in IPCN #12477.

In order to continue to fully support our customer's requirements for High Frequency Transistors, the fabrication of these devices is being moved from ON Semiconductor's current subcontractor wafer fab, Panjit in Phoenix Arizona to ON Semiconductor's internal wafer fab ISMF in Seremban, Malaysia.

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RELIABILITY DAT	A SUN	MMARY:
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High Temp Reverse Bias (HTRB) Ta=150C, VCEs =32, 1008 hrs 0/308

Intermittent Op Life (IOL)

Ta=25C, delta Tj=100 deg C max, Ton=Toff = 2min 15000 cyc 0/308

Temperature Cycling (TC) Ta= -65/150 deg C 1000 cyc 0/308

Autoclave (AC) Ta=121C, RH=100%, ~15psig 96 hours 0/308

High Temp High Humidity Reverse Bias (H3TRB)

Ta=85 deg C, RH= 85%, VCEs = 32V 1008 hours 0/308

De-processing Analysis post TC (DPA) 0/8

De-processing Analysis post H3TRB (DPA) 0/8

Electrostatic Discharge (ESD)

 \mbox{HBM} \mbox{Class} 2B \mbox{MM} \mbox{Class} C

ELECTRICAL CHARACTERISTIC SUMMARY:

Datasheet specifications remain unchanged.

CHANGED PART IDENTIFICATION:

Parts with date code after 0525 may be sourced from either site.

AFFECTED DEVICE LIST (WITHOUT SPECIALS): PART

BSV52LT1

MMBT2369ALT1

MMBT2369ALT1G

MMBT2369ALT3

MMBT2369ALT3G

MMBT2369LT1

MMBT2369LT1G

MMPQ2369

MMPQ2369R2

MPS2369

MPS2369A

MPS2369AG

MPS2369ARLRP

MPS2369RLRA

MPS3646

MPS3646G

MPS3646RLRA

NST2369ADW1T1

P2N2369ZL1

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